

CURRICULUM VITAE

Name, Family name : Miyamoto Forename: Yasuyuki
Sex: Male
Date of birth: 12 February, 1961
Place of birth: Tokyo, Japan
Nationality: Japanese
Mailing address: Department of Physical Electronics,
Tokyo Institute of Technology,
2-12-1-S9-2, O-okayama, Meguro-ku,
Tokyo 152, Japan
Telephone and Facsimile No.: Tel: +81-3-5734-2572 Fax:+81-3-5734-2907
e-mail: miya@pe.titech.ac.jp



Education:

- 1979-1983 Department of Physical Electronics, Tokyo Institute of Technology
Awarded the degree of B.Eng. in physical electronics.
- 1983-1985 Department of Physical Electronics, Tokyo Institute of Technology
Awarded the degree of M.Eng. in physical electronics for a thesis entitled
"Improvement of Crystal Quality of GaInAsP/InP grown by OMVPE"
supervised by Professor Yasuharu SUEMATSU and Professor Kazuhito FURUYA.
- 1985-1988 Department of Physical Electronics, Tokyo Institute of Technology
Awarded the degree of D.Eng. in physical electronics for a thesis entitled
"GaInAsP/InP Organometallic Vapor Phase Epitaxy (OMVPE) for Quantum Box
Lasers"
supervised by Professor Yasuharu SUEMATSU and Professor Kazuhito FURUYA.

Research and professional experience:

- 1988-1992 Research Associate at the Department of Electrical and Electronics Engineering,
Tokyo Institute of Technology working with Professor Kazuhito FURUYA on
Electron Devices.
- 1992-2000 Associate Professor at the Department of Electrical and Electronics Engineering,
Tokyo Institute of Technology working with Professor Kazuhito FURUYA on
Electron Devices.
- 1994-1995 Consultant of AT&T Bell laboratories, Holmdel, NJ.
- 2000-present Associate Professor at the Department of Physical Electronics, Tokyo Institute of
Technology working with Professor Kazuhito FURUYA on Electron Devices.
- 2002-2007 Coordinator of Tokyo Tech's Nano Foundry service as a part of nanotechnology
researchers network by Ministry of Education, Culture, Sports, Science and
Technology.
- 2007-present Coordinator of Tokyo Tech's Nano Foundry service as a part of nanotechnology
network project by Ministry of Education, Culture, Sports, Science and Technology.

Membership of learned societies:

The Japan Society of Applied Physics (Deputy from 2003 to 2007)
The Institute of Electronics, Information and Communication Engineers (IEICE), Senior Memembr
The Institute of Electrical Engineers of Japan
The Institute of Electrical and Electronics Engineers (EDS and SSC), Senior Memembr
American Vacuum Society

International commitments

Editor of Japanese Journal of Applied Physics (JJAP), from 2001 to 2004..
Head editor of JJAP, from 2004.to 2009.
Editor of Trans IEICE of JAPAN from 1996 to 1998
IEEE EDS Distinguished Lecturer (Dec. 2004 – present)
Technical Program Committee Member of Device Research Conference (DRC) from 2000 to
2002.

Subcommittee chair (Electron devices) in Program Committee of 2010 Int. Conf. on Indium Phosphide and Related Materials (IPRM)
Program Committee Member of IPRM in 2001, 2003, 2008
Subcommittee chair (Electron- and Ion-Beam Lithography) in Program Committee of 2009 Microprocesses and Nanotechnology Conf. (MNC) from 2002 to 2004.
Program Committee Member of MNC from 2002 to 2004.
Subcommittee chair (Transport devices) in program committee of 2007 International Symposium of Compound Semiconductor (ISCS)
Program Committee Member of SSDM from 2001 and 2004, 2009.
Chairperson of Editorial committee for the special issue of SSDM in JJAP, 2005.
Program Committee Member of TWHM from 2000 to 2009.
Program Committee Member of IEEE Nanotechnology Materials and Devices Conference in 2008.

Awards:

Tejima Encourage Award
Young Scientists and Engineers Award for the 1988 MRS International Meeting
APEX/JJAP Editorial Contribution Award

Technical experiences:

Design, fabrication and measurement of devices (LD, HET, RTD, HBT)
Fabrication technology for ultra-fine structure
(Electron beam lithography, Interference lithography, X-ray lithography)
Design and installation of apparatuses
(4 OMVPE, 1 SiO₂ CVD, 1 ECR-RIBE, 1 X-ray lithography system)

Current Interests:

High-speed operation of InP Heterojunction Bipolar Transistors
InP Hot Electron Transistors for high-speed operation.
Interference of hot electron in semiconductors
Line edge roughness of electron beam resist for fine pattern.
Residual impurity in OMVPE for higher mobility

Publications: Over 90 papers in international journals with judge.

Patents: 5 US patents (issued), 7 Japanese patents (applied for)

Language: fairly good in English